

# **isc** Silicon NPN Darlington Power Transistor

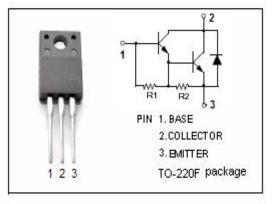
# 2SD1826

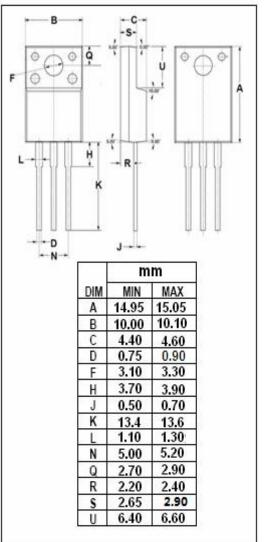
### DESCRIPTION

- High DC Current Gain-
- : h<sub>FE</sub>= 2000(Min)@ (V<sub>CE</sub>= 2V, I<sub>C</sub>= 3.5A)
- Large Current Capability and Wide ASO.
- Complement to Type 2SB1224

### **APPLICATIONS**

• Designed for use in control of motor drivers, printer hammer drivers, relay drivers, and constant-voltage regulators.





### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	70	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V	
V <sub>EBO</sub>	Emitter-Base Voltage	V		
lc	Collector Current-Continuous	7	А	
Ісм	Collector Current-Peak	10	А	
Pc	Collector Power Dissipation @T <sub>a</sub> =25℃	2	10/	
	Collector Power Dissipation @T <sub>C</sub> =25℃	25	W	
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature	-55~150	°C	

isc website: <u>www.iscsemi.com</u>



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### ELECTRICAL CHARACTERISTICS

#### Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; R <sub>BE</sub> = ∞	60			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 5mA; I <sub>E</sub> = 0	70			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3.5A; I <sub>B</sub> = 7mA			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 3.5A; I <sub>B</sub> = 7mA			2.0	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 40V; I <sub>E</sub> = 0			100	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			3.0	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 3.5A; V <sub>CE</sub> = 2V	2000	5000		
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 3.5A; V <sub>CE</sub> = 5V		20		MHz
Switching Times						
t <sub>on</sub>	Turn-on Time			0.6		μ <b>S</b>

t <sub>on</sub>	Turn-on Time		0.6	μ <b>S</b>
t <sub>stg</sub>	Storage Time	$I_{C}$ = 3A, $I_{B1}$ = - $I_{B2}$ = 6mA, V <sub>CC</sub> = 20V; R <sub>L</sub> = 6.7 Ω	3.0	μ S
tf	Fall Time		1.7	μ <b>S</b>

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